

Fig. Developed HfON(O<sub>3</sub>) and HfON(IPA) / InGaAs MOS C-V characteristics

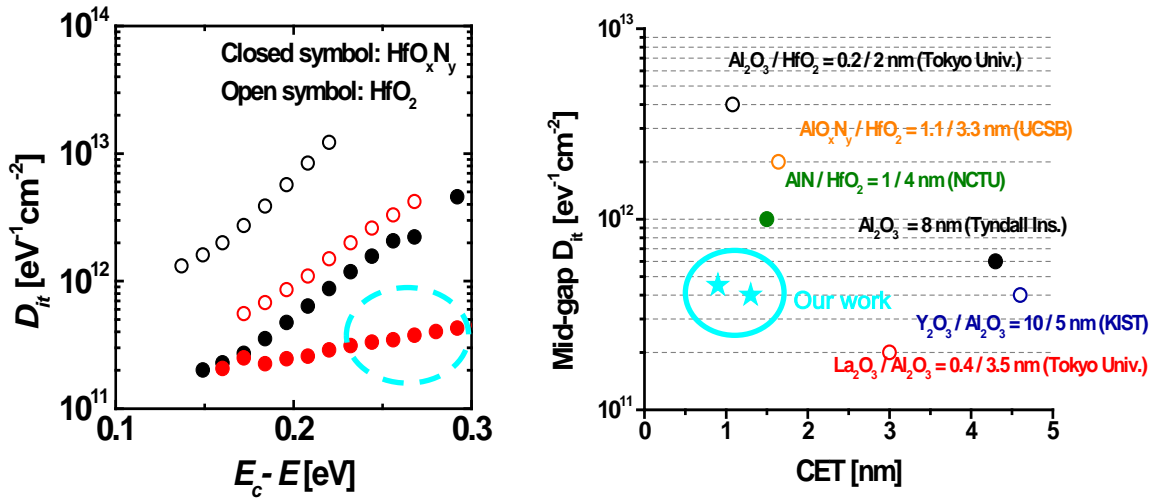


Fig.  $D_{it}$  (black:O<sub>3</sub> and red:IPA) and comparison to other research groups

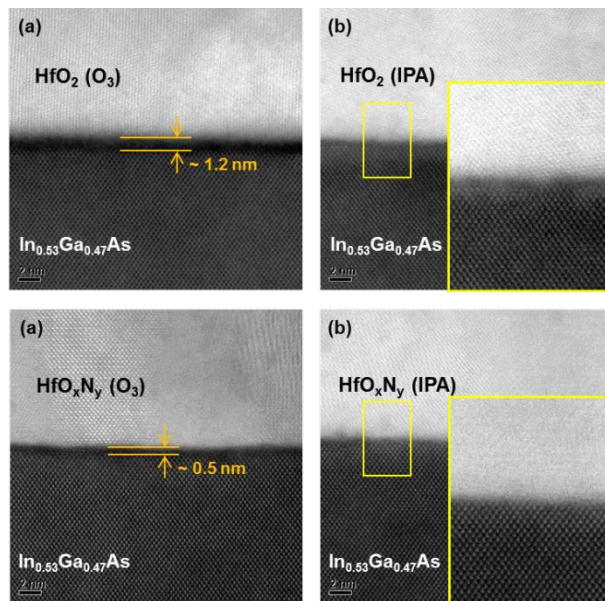


Fig. STEM images of each ALD process conditions